

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
-30V	105mΩ@-10V	-1.8A
	160mΩ@-4.5V	

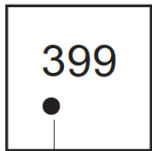
**Feature**

- High power and current handing capability

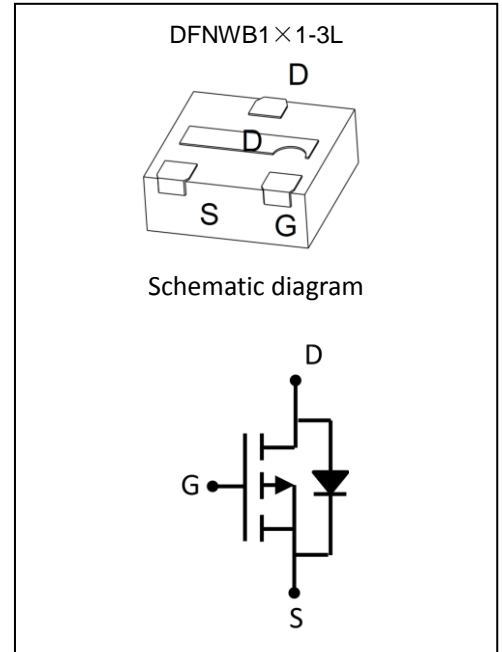
**Application**

- Load Switch for Portable Devices
- PWM applications

**MARKING:**



PIN 1



**ABSOLUTE MAXIMUM RATINGS ( $T_a=25^{\circ}C$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	-1.8	A
Pulsed Drain Current	$I_{DM}$	-5.0	A
Power Dissipation	$P_D$	0.2	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	625	$^{\circ}C/W$
Junction Temperature	$T_J$	150	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55~ +150	$^{\circ}C$

**MOSFET ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$  unless otherwise noted)**

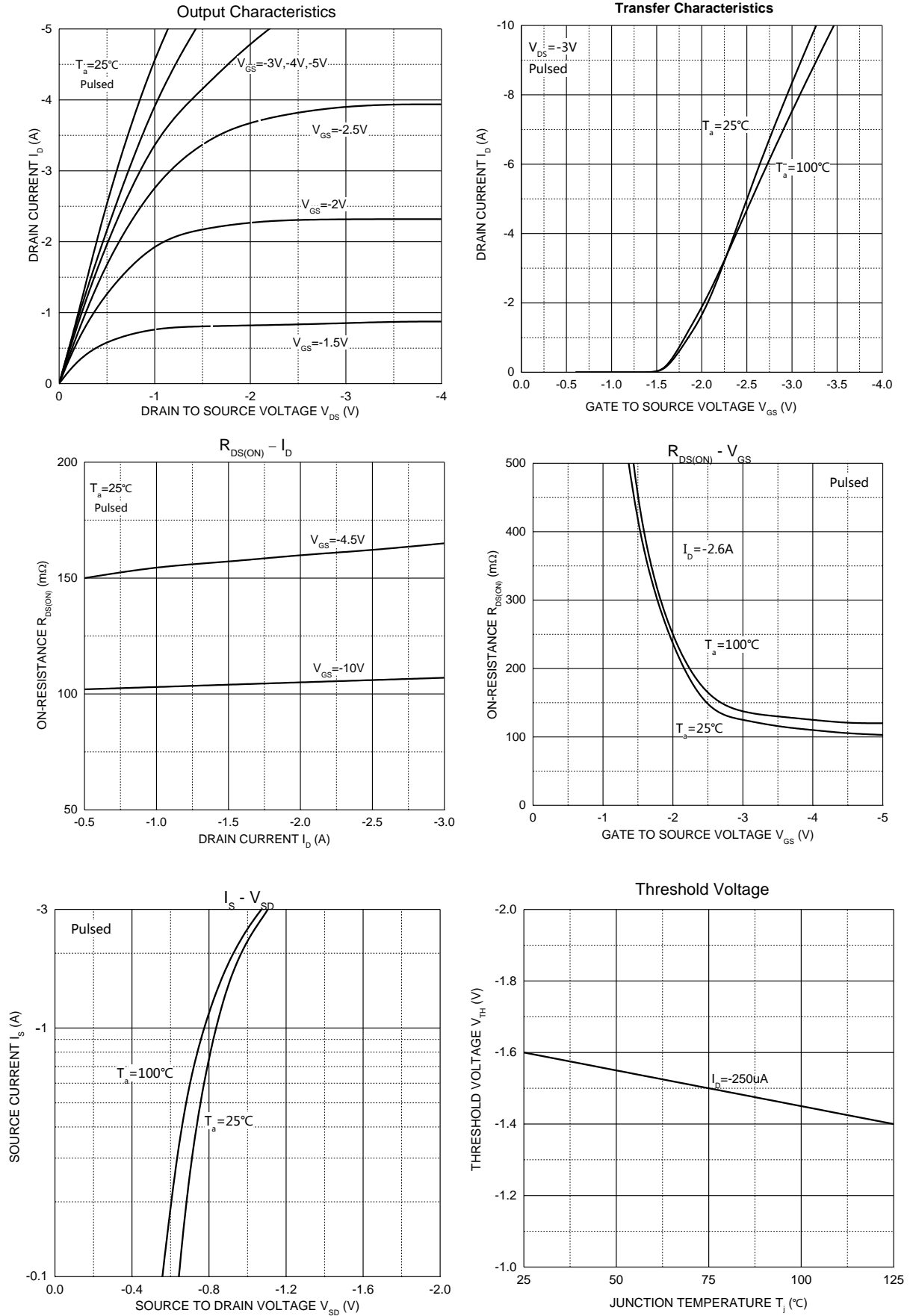
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -30V, V_{GS} = 0V$			-1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.6	-2.4	V
Drain-source on-resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -2A$		105	130	m $\Omega$
		$V_{GS} = -4.5V, I_D = -2A$		160	190	
Forward transconductance <sup>a</sup>	$g_{FS}$	$V_{DS} = -5V, I_D = -2A$	1	3.8		S
<b>Dynamic characteristics<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		290		pF
Output Capacitance	$C_{oss}$			60		
Reverse Transfer Capacitance	$C_{rss}$			34		
Total Gate Charge	$Q_g$	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -2A$		3.0		nC
Gate-Source Charge	$Q_{gs}$			0.5		
Gate-Drain Charge	$Q_{gd}$			0.8		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -10V, R_L = 5\Omega,$ $V_{GEN} = -4.5V, R_g = 3\Omega$		10		ns
Turn-on rise time	$t_r$			5.0		
Turn-off delay time	$t_{d(off)}$			21		
Turn-off fall time	$t_f$			7		
<b>Source-Drain Diode characteristics</b>						
Diode forward current	$I_S$	$T_C = 25^\circ\text{C}$			-1.5	A
Diode Forward voltage	$V_{DS}$	$V_{GS} = 0V, I_S = -2.0A$			-1.2	V

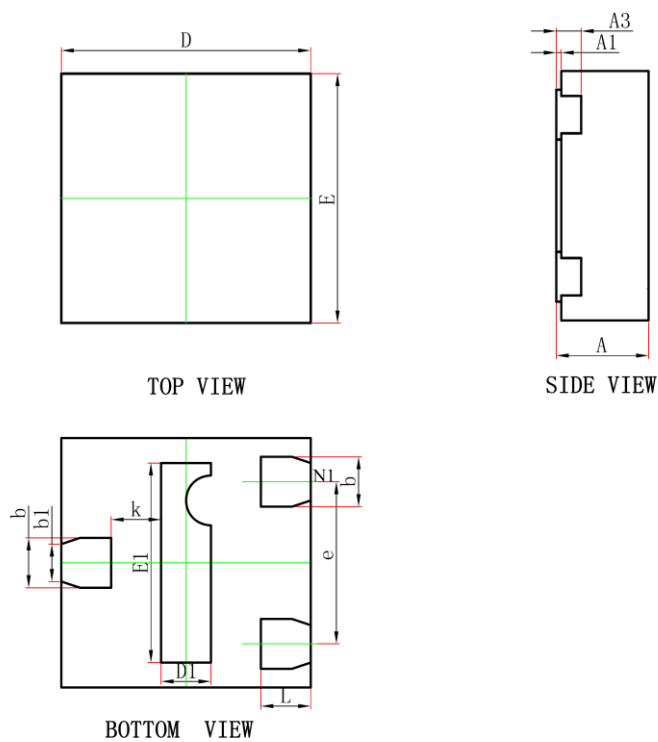
Notes :

a. Pulse Test : Pulse Width < 300 $\mu s$ , Duty Cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

**Typical Electrical and Thermal Characteristics**

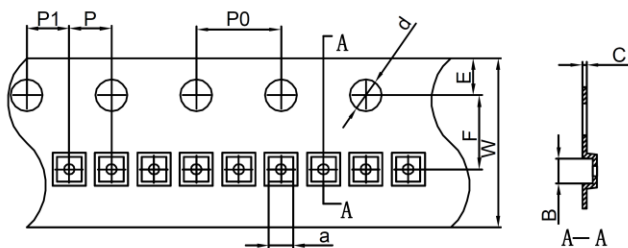


**DFNWB1 × 1-3L Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN.	MAX.	MIN.	MAX.
A	0.340	0.400	0.013	0.016
A1	0.000	0.050	0.000	0.002
A3	0.102REF.		0.004REF.	
D	0.900	1.100	0.035	0.043
E	0.900	1.100	0.035	0.043
D1	0.100	0.300	0.004	0.012
E1	0.700	0.900	0.028	0.035
b	0.150	0.250	0.006	0.010
b1	0.150REF.		0.006REF.	
e	0.650BSC.		0.026BSC.	
k	0.200REF.		0.008REF.	
L	0.124	0.276	0.005	0.011

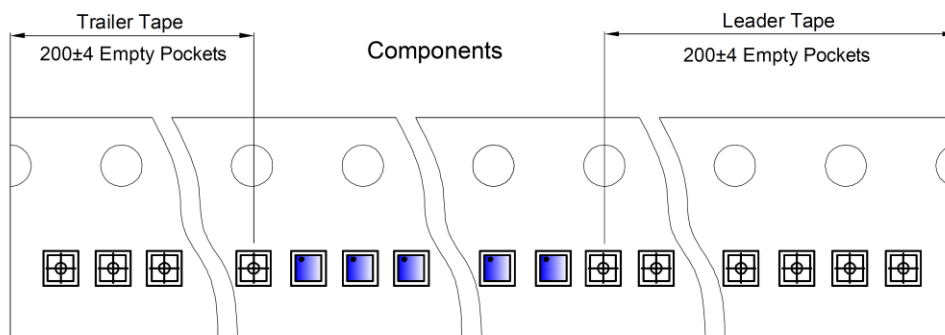
## DFNWB1 × 1-3L Tape and Reel

### DFNWB1x1-3L Embossed Carrier Tape

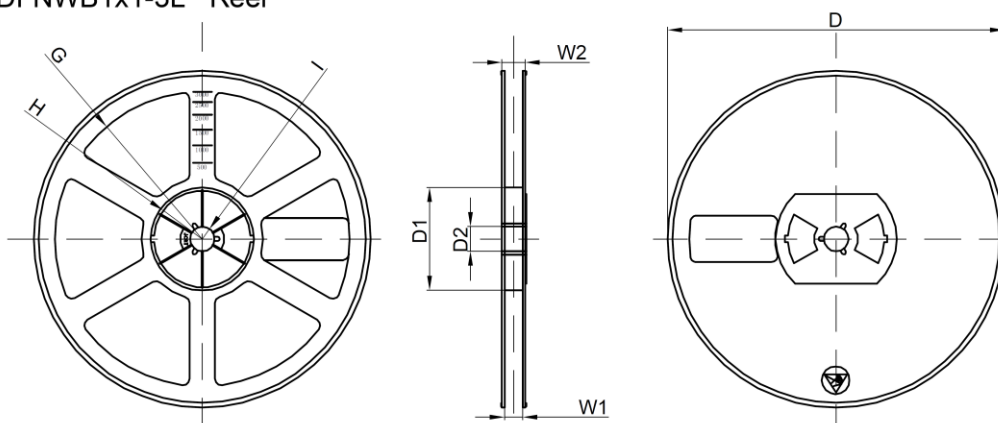


Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
DFNWB1x1-3L	1.16	1.16	0.20	Ø1.50	1.75	3.50	4.00	2.00	2.00	8.00

### DFNWB1x1-3L Tape Leader and Trailer



### DFNWB1x1-3L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	φ180.00	60.00	13.00	R78.00	R25.60	R6.50	9.50	13.10

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
10000 pcs	7 inch	100,000 pcs	203×203×195	400,000pcs	438×438×220	

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)